

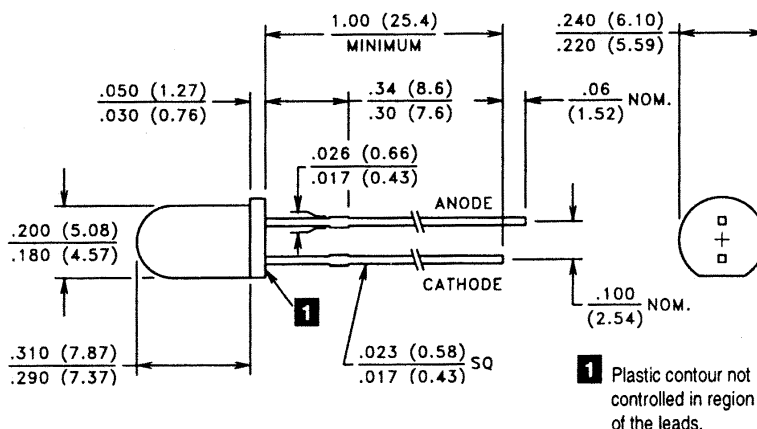
GaAlAs Infrared Emitting Diodes

T-1 $\frac{3}{4}$ (5 mm) Plastic Package — 880 nm

VTE1281-1H, -2H



PACKAGE DIMENSIONS inch (mm)



DESCRIPTION

CASE 26 T-1 $\frac{3}{4}$ (5 mm)
CHIP SIZE: .015" x .015"

This narrow beam angle 5 mm diameter plastic packaged emitter contains a medium area, single wirebonded, GaAlAs, 880 nm, high efficiency IRED chip. It is designed to be cost effective in moderate pulse drive applications.

RoHS Compliant



ABSOLUTE MAXIMUM RATINGS @ 25°C (unless otherwise noted) ■

Maximum Temperatures		Maximum Reverse Voltage:	5.0V
Storage and Operating:	-40°C to 100°C	Maximum Reverse Current @ $V_R = 5V$:	10 μA
Continuous Power Dissipation:	200 mW	Peak Wavelength (Typical):	880 nm
Derate above 30°C:	2.86 mW/°C	Junction Capacitance @ 0V, 1 MHz (Typ.):	23 pF
Maximum Continuous Current:	100 mA	Response Time @ $I_F = 20$ mA	
Derate above 30°C:	1.43 mA/°C	Rise: 1.0 μs Fall: 1.0 μs	
Peak Forward Current, 10 μs , 100 pps:	2.5 A	Lead Soldering Temperature:	260°C
Temp. Coefficient of Power Output (Typ.):	-.8%/°C	(1.6 mm from case, 5 seconds max.)	

ELECTRO-OPTICAL CHARACTERISTICS @ 25°C (See also GaAlAs curves, pages 108-110)

Part Number ■	Output						Forward Drop		Half Power Beam Angle
	Irradiance				Radiant Intensity	Total Power	Test Current	V_F	
	E_e		Condition		I_e	P_O	I_{FT}	@ I_{FT}	
	mW/cm ²		distance	Diameter	mW/sr	mW	mA (Pulsed)	Volts	Typ.
	Min.	Typ.	mm	mm	Min.	Typ.		Typ. Max.	
VTE1281-1H	2.5	3.3	36	6.4	32	20	100	1.5 2.0	$\pm 10^\circ$
VTE1281-2H	5.0	6.5	36	6.4	65	25	100	1.5 2.0	$\pm 10^\circ$

■ Refer to General Product Notes, page 2.